

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

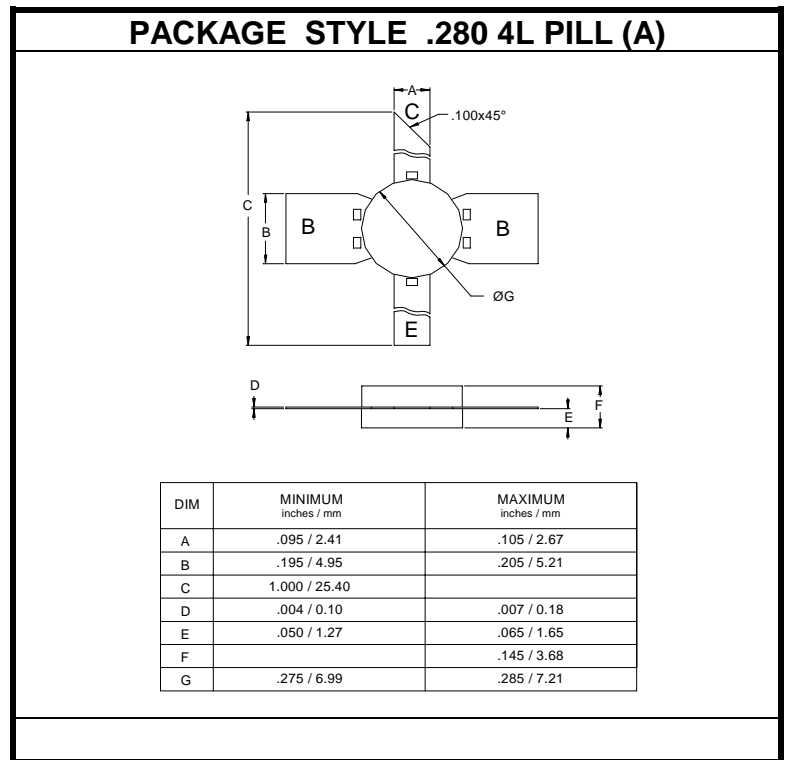
The **ASI MRF1035MB** is Designed for Class C, DME/TACAN Applications up to 1090 MHz.

FEATURES:

- Internal Input Matching Network
- $P_G = 10$ dB at 35 W/1090 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	2.0 A
V_{CBO}	60 V
V_{CES}	60 V
P_{DISS}	35 W PEAK
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	5.0 °C/W


CHARACTERISTICS $T_C = 25$ °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 20$ mA	60			V
BV_{CES}	$I_C = 20$ mA	60			V
BV_{EBO}	$I_E = 2.0$ mA	4.0			V
I_{CBO}	$V_{CE} = 50$ V			2.0	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 500$ mA	10		100	---
C_{ob}	$V_{CB} = 50$ V $f = 1.0$ MHz		10	15	pF
P_G	$V_{CC} = 50$ V $P_{OUT} = 35$ W $f = 1090$ MHz	10	12.4		dB
η_c		30	34		%